

I claim

1. A cathode structure for a vacuum sputtering machine, which comprise:
an assistant magnetic field generating device being connected to the
mechanical structure of the vacuum sputtering machine, and having the ability
5 to generate the assistant magnetic field;

a target bar being connected to the cathode of a electrical field, the target
bar having a inner side surface, a outer side surface, the inner side surface
facing the assistant magnetic field generating device, and the outer side surface
facing the bombardment electrical particles of the vacuum sputtering machine;
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an interference magnetic strip being made of magnetic material and placed
at the position between the target bar and the assistant magnetic field
generating device;

whereby the effect of the interference magnetic strip can interfere the
15 assistant magnetic field, the bombardment electrical particles can bombard the
target bar more uniform.

2. The cathode structure for a vacuum sputtering machine as claimed in
claim 1, further comprises a connection carrier plate being positioned between
20 the target bar and the assistant magnetic field generating device, and the
interference magnetic strip being installed in the connection carrier plate

3. The cathode structure for a vacuum sputtering machine as claimed in
claim 2, further comprises an Indium connection structure placed between the

target bar and the connection carrier plate.

4. The cathode structure for a vacuum sputtering machine as claimed in claim 2, further comprises an elastic fastening mechanism to fasten the target
5 bar on the connection carrier plate.

5. The cathode structure for a vacuum sputtering machine as claimed in claim 1, wherein the interference magnetic strip is made by the permanent magnet
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6. The cathode structure for a vacuum sputtering machine as claimed in claim 1, wherein the interference magnetic strip is made by the temporary magnetism material
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